Schottky Barrier Diodes

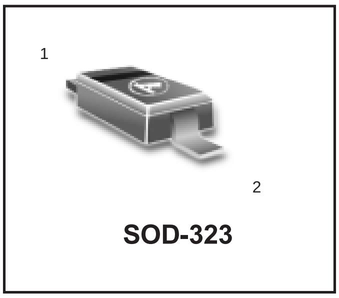
LBAT54HT1G
S- LBAT54HT1G

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- Extremely Fast Switching Speed
- Low Forward Voltage — 0.35 Volts (Typ) @ I_F = 10 mAdc
- Device Marking: JV

We declare that the material of product compliance with RoHS requirements.

S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



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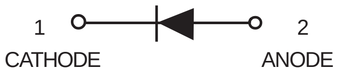


ORDERING INFORMATION

Device	Marking	Shipping
LBAT54HT1G	JV	3000/Tape & Reel
LBAT54HT3G	JV	10000/Tape & Reel

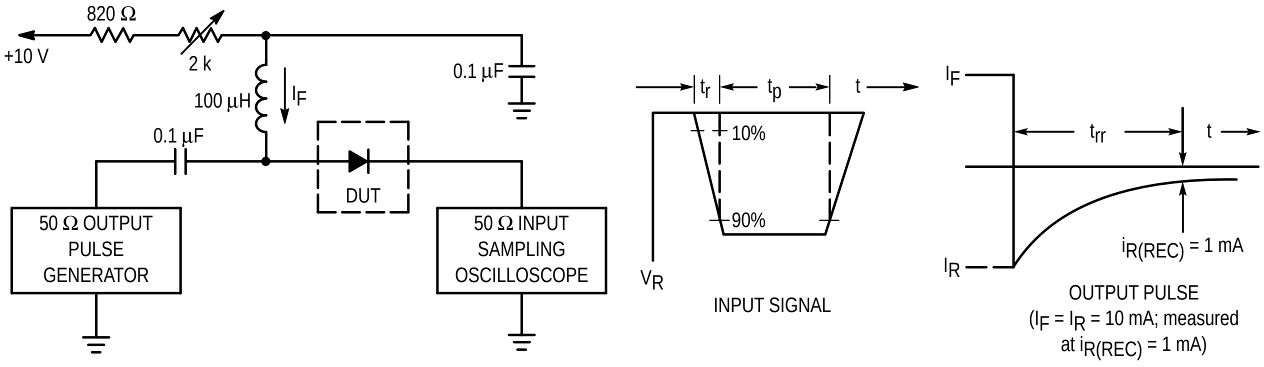
MAXIMUM RATINGS (T$_J$ =125°C unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Total Device Dissipation FR-5 Board,* T_A = 25°C	P_D	200	mW
Derate above 25°C		1.57	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	°C/W
Junction Temperature	T_J	125Max	°C
Storage Temperature Range	T_{stg}	–55 to +150	°C

* FR-4 Minimum Pad

ELECTRICAL CHARACTERISTICS (T$_A$ = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 µA)	$V_{(BR)R}$	30	—	—	Volts
Total Capacitance (V_R = 1.0 V, f = 1.0 MHz)	C_T	—	—	10	pF
Reverse Leakage (V_R = 25 V)	I_R	—	0.5	2.0	µAdc
Forward Voltage (I_F = 0.1 mAdc)	V_F	—	0.22	0.24	Vdc
Forward Voltage (I_F = 30 mAdc)	V_F	—	0.41	0.5	Vdc
Forward Voltage (I_F = 100 mAdc)	V_F	—	0.52	1	Vdc
Reverse Recovery Time (I_F = I_R = 10 mAdc, $I_{R(REC)}$ = 1.0 mAdc, Figure 1)	t_{rr}	—	—	5.0	ns
Forward Voltage (I_F = 1.0 mAdc)	V_F	—	0.29	0.32	Vdc
Forward Voltage (I_F = 10 mAdc)	V_F	—	0.35	0.40	Vdc
Forward Current (DC)	I_F	—	—	200	mAdc
Repetitive Peak Forward Current	I_{FRM}	—	—	300	mAdc
Non–Repetitive Peak Forward Current (t < 1.0 s)	I_{FSM}	—	—	600	mAdc



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. t_p >> t_{rr}

Fig.1 RECOVERY TIME EQUIVALENT TEST CIRCUIT

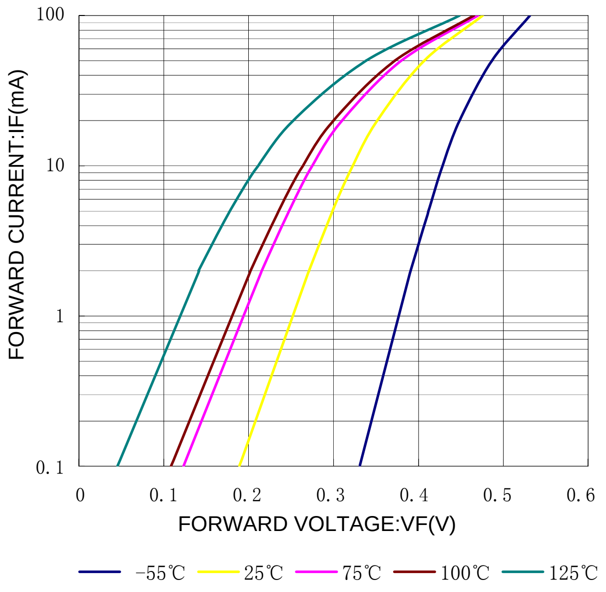


Fig.2 FORWARD CHARACTERISTICS

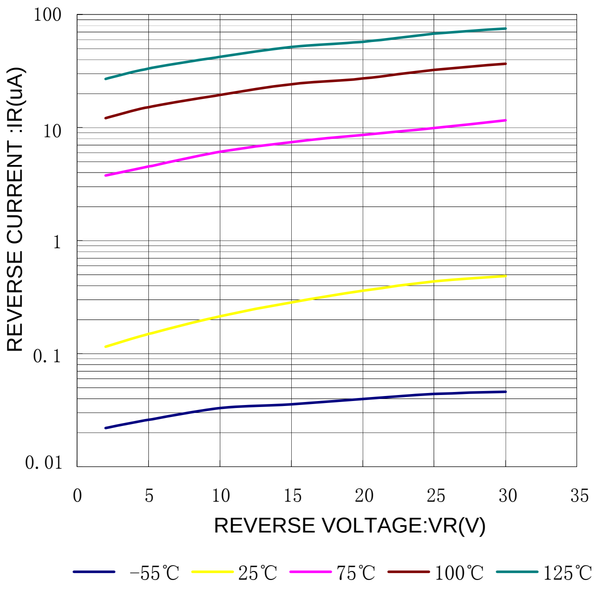


Fig.3 REVERSE CHARACTERISTICS

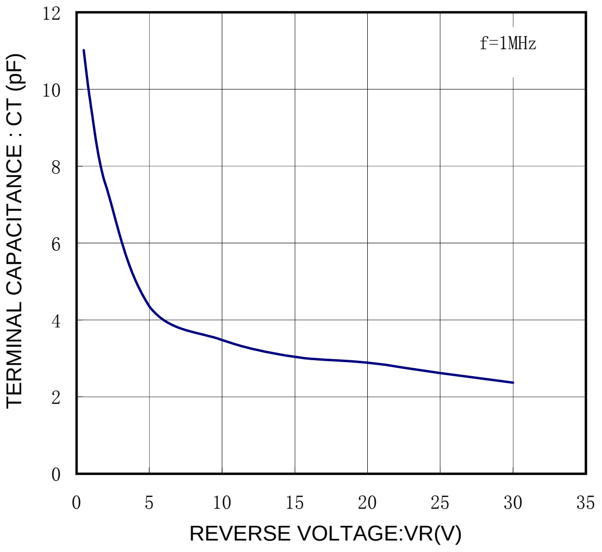


Fig.4 VR-CT CHARACTERISTICS

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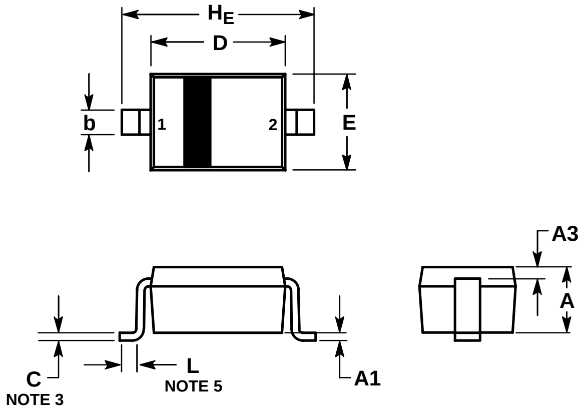

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			**INCHES**		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H_E	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*